

# RJK6013DPE

600V - 11A - MOS FET High Speed Power Switching R07DS0486EJ0200 (Previous: REJ03G1535-0100) Rev.2.00

Jun 21, 2012

#### **Features**

• Low on-resistance  $R_{DS(on)} = 0.58~\Omega~typ.~(at~I_D = 5.5~A,~V_{GS} = 10~V,~Ta = 25^{\circ}C)$ 

- Low leakage current
- High speed switching

#### **Outline**

RENESAS Package code: PRSS0004AE-B
(Package name: LDPAK(S)-(1) )

1. Gate
2. Drain
3. Source
4. Drain

### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item  | Symbol                        | Ratings     | Unit |
|---|-------------------------------|-------------|------|
| Drain to source voltage                     | V <sub>DSS</sub>              | 600         | V    |
| Gate to source voltage                      | V <sub>GSS</sub>              | ±30         | V    |
| Drain current                               | I <sub>D</sub>                | 11          | Α    |
| Drain peak current                          | I <sub>D (pulse)</sub> Note1  | 33          | Α    |
| Body-drain diode reverse drain current      | I <sub>DR</sub>               | 11          | Α    |
| Body-drain diode reverse drain peak current | I <sub>DR (pulse)</sub> Note1 | 33          | Α    |
| Avalanche current                           | I <sub>AP</sub> Note3         | 4           | Α    |
| Avalanche energy                            | E <sub>AR</sub> Note3         | 0.87        | mJ   |
| Channel dissipation                         | Pch Note2                     | 100         | W    |
| Channel to case thermal impedance           | θch-c                         | 1.25        | °C/W |
| Channel temperature                         | Tch                           | 150         | °C   |
| Storage temperature                         | Tstg                          | -55 to +150 | °C   |

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tc = 25°C
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

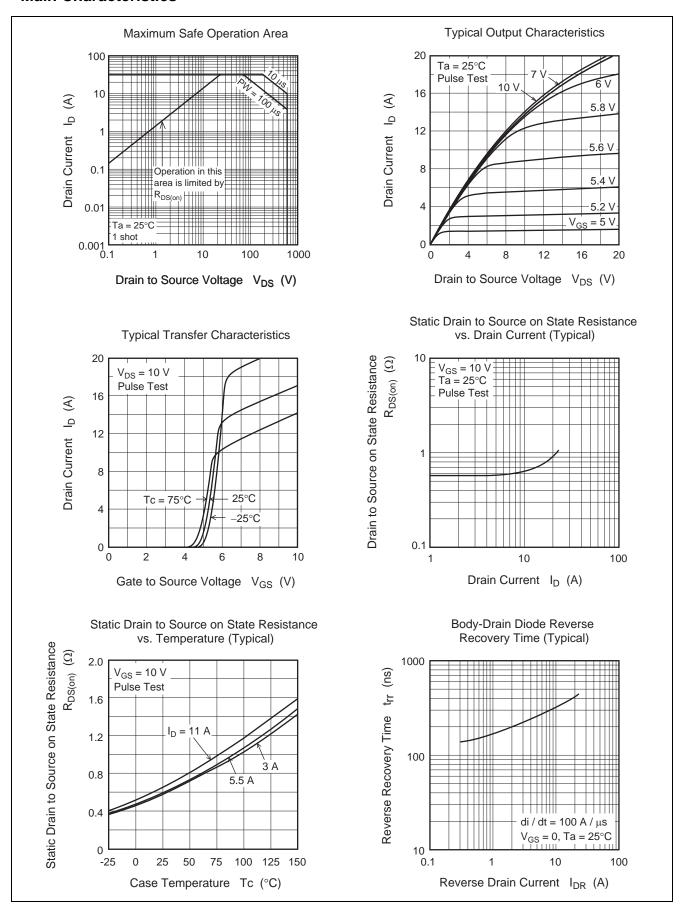
### **Electrical Characteristics**

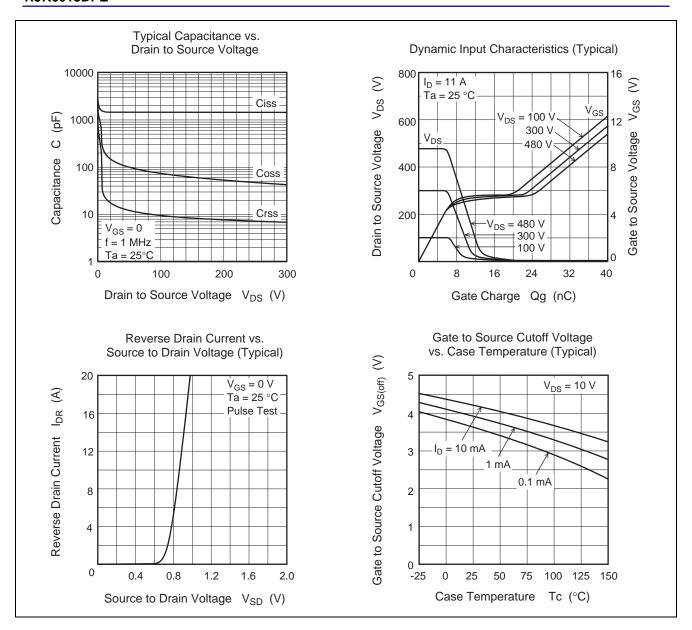
 $(Ta = 25^{\circ}C)$ 

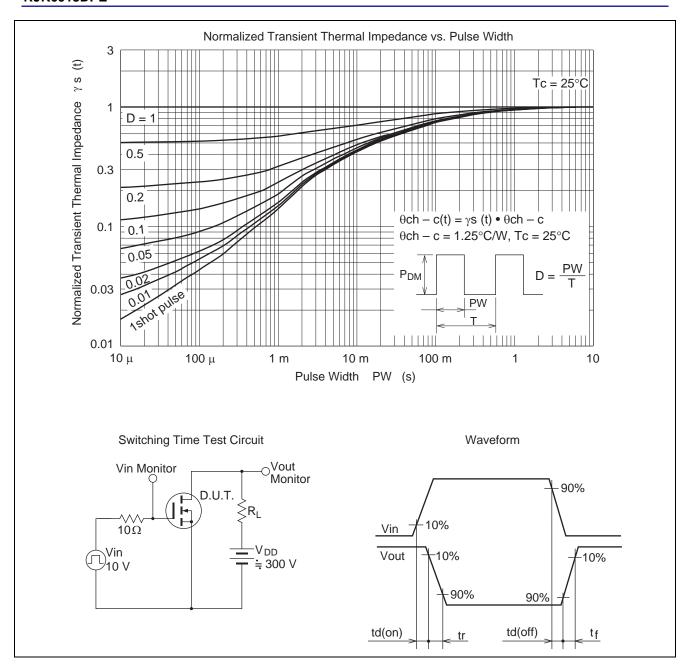
| Item                                       | Symbol              | Min | Тур  | Max  | Unit | Test conditions  |
|--|---------------------|-----|------|------|------|--|
| Drain to source breakdown voltage          | $V_{(BR)DSS}$       | 600 | _    | _    | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$  |
| Zero gate voltage drain current            | I <sub>DSS</sub>    | _   | _    | 1    | μΑ   | $V_{DS} = 600 \text{ V}, V_{GS} = 0$   |
| Gate to source leak current                | I <sub>GSS</sub>    | _   | _    | ±0.1 | μА   | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$  |
| Gate to source cutoff voltage              | $V_{GS(off)}$       | 3.0 | _    | 4.5  | V    | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$                                      |
| Static drain to source on state resistance | R <sub>DS(on)</sub> | _   | 0.58 | 0.70 | Ω    | $I_D = 5.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$                        |
| Input capacitance                          | Ciss                | _   | 1450 | _    | pF   | V <sub>DS</sub> = 25 V<br>V <sub>GS</sub> = 0<br>f = 1 MHz                         |
| Output capacitance                         | Coss                | _   | 140  | _    | pF   |  |
| Reverse transfer capacitance               | Crss                | _   | 17   | _    | pF   |  |
| Turn-on delay time                         | $t_{d(on)}$         | _   | 33   | _    | ns   | $I_D = 5.5 \text{ A}$ $V_{GS} = 10 \text{ V}$ $R_L = 54.5 \Omega$ $Rg = 10 \Omega$ |
| Rise time                                  | t <sub>r</sub>      | _   | 20   | _    | ns   |  |
| Turn-off delay time                        | $t_{d(off)}$        | _   | 87   | _    | ns   |  |
| Fall time                                  | t <sub>f</sub>      | _   | 15   | _    | ns   |  |
| Total gate charge                          | Qg                  | _   | 37.5 | _    | nC   | $V_{DD} = 480 \text{ V}$ $V_{GS} = 10 \text{ V}$ $I_D = 11 \text{ A}$              |
| Gate to source charge                      | Qgs                 | _   | 7.3  | _    | nC   |  |
| Gate to drain charge                       | Qgd                 | _   | 16.4 | _    | nC   |  |
| Body-drain diode forward voltage           | $V_{DF}$            | _   | 0.87 | 1.45 | V    | I <sub>F</sub> = 11 A, V <sub>GS</sub> = 0 Note4                                   |
| Body-drain diode reverse recovery time     | t <sub>rr</sub>     | _   | 350  | _    | ns   | $I_F = 11 \text{ A}, V_{GS} = 0$<br>$di_F/dt = 100 \text{ A}/\mu\text{s}$          |

Notes: 4. Pulse test

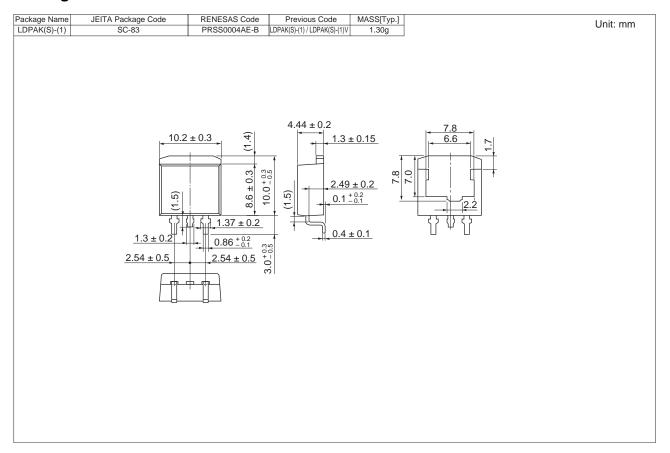
### **Main Characteristics**







### **Package Dimensions**



## **Ordering Information**

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RJK6013DPE-00#J3      | 1000 pcs | Taping             |

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